Abstract Submitted for the SHOCK13 Meeting of The American Physical Society

Uniaxial pressure effect of Metal-Insulator Transition (T_{MI}) in oriented $Sm_{0.55}(Sr_{0.5}Ca_{0.5})_{0.45}MnO_3^1$ SONACHALAM ARUMUGAM, D. MO-HAN RADHEEP, Centre for High Pressure Research, Bharathidasan University, P. SARKAR, P. MANDAL, Saha Institute of Nuclear Physics, Kolkata, ARUMUGAM TEAM, PRABHAT MANDAL COLLABORATION — Perovskite type manganites $R_{1-x}A_xMnO_3$ (R: rare earth ions, A: alkaline earth ions) exhibit various fundamental phenomena like colossal magnetoresistance (CMR), phase separation, and first-order ferromagnetic (FM) to paramagnetic (PM) phase transition etc. Similar to CMR, piezoresistance (PR), the change in electrical resistance in response to external pressure, can also be important parameter for various technological applications. Several studies shows that the order of phase transition can be changed either by applying external perturbations like magnetic field, pressure (P), etc. or internally like doping etc. SSCMO single crystal was grown using floating zone technique and the quality was carefully checked and aligned along the c axis as well as ab-plane. We have investigated the effect of uniaxial pressure (P) on electrical resistivity along the ab-plane and c-axis in a single crystal of SSCMO. A huge $PR \sim 10^7 \%$ at P = 90MPa and a remarkable increase ($\sim 79~K/GPa$) of T_{MI} have been observed with the application of $P \mid |c-axis|$, while T_{MI} decreases at the rate of $\sim 77 \ K/GPa$ for $P \perp c$ axis. These values of PR and dT_{MI}/dP are much larger than those observed in other perovskite and bilayer manganites. Hence, these materials may be used for various technological applications.

¹The authors SA and DMR wishes to thank DST, UGC and CSIR-SRF scheme (India) for the financial support to carry out the research work

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Date submitted: 12 Feb 2013 Electronic form version 1.4